

CMLD6001DO

**SURFACE MOUNT
DUAL, ISOLATED, OPPOSING
ULTRA LOW LEAKAGE
SILICON SWITCHING DIODES**



www.centrasemi.com

PICOmini™



SOT-563 CASE

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMLD6001DO type contains Two (2) Isolated Opposing Configuration, Silicon Switching Diodes, manufactured by the epitaxial planar process, epoxy molded in a PICOmini™ surface mount package. These devices are designed for switching applications requiring extremely low leakage.

MARKING CODE: C60

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Continuous Reverse Voltage
Peak Repetitive Reverse Voltage
Continuous Forward Current
Peak Forward Surge Current, $t_p=1.0\mu\text{s}$
Peak Forward Surge Current, $t_p=1.0\text{s}$
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V_R	75
V_{RRM}	100
I_F	250
I_{FSM}	4.0
I_{FSM}	1.0
P_D	250
T_J, T_{stg}	-65 to +150
θ_{JA}	500

UNITS

V
V
mA
A
A
mW
$^\circ\text{C}$
$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ\text{C}$ unless otherwise noted)

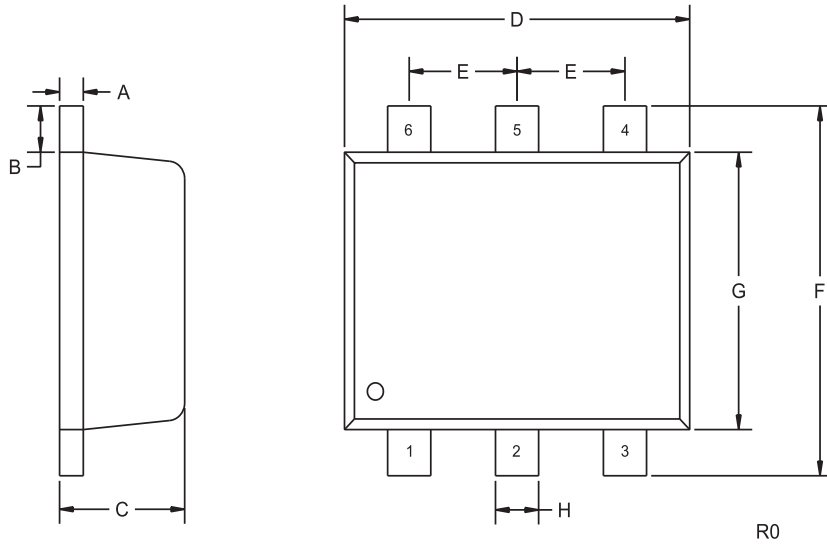
SYMBOL	TEST CONDITIONS			UNITS
		MIN	MAX	
I_R	$V_R=75\text{V}$		500	pA
BV_R	$I_R=100\mu\text{A}$	100		V
V_F	$I_F=1.0\text{mA}$		0.85	V
V_F	$I_F=10\text{mA}$		0.95	V
V_F	$I_F=100\text{mA}$		1.1	V
C_T	$V_R=0, f=1.0\text{MHz}$		2.0	pF
t_{rr}	$I_R=I_F=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$		3.0	μs

R3 (9-May 2011)

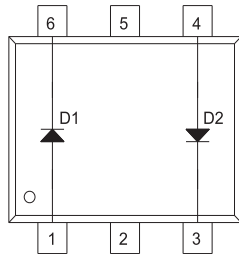
CMLD6001DO
SURFACE MOUNT
DUAL, ISOLATED, OPPOSING
ULTRA LOW LEAKAGE
SILICON SWITCHING DIODES



SOT-563 CASE - MECHANICAL OUTLINE



PIN CONFIGURATION



LEAD CODE:

- 1) Anode D1
- 2) NC
- 3) Cathode D2
- 4) Anode D2
- 5) NC
- 6) Cathode D1

MARKING CODE: C60

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.007	0.10	0.18
B	0.008		0.20	
C	0.022	0.024	0.56	0.60
D	0.059	0.067	1.50	1.70
E	0.020		0.50	
F	0.061	0.067	1.55	1.70
G	0.047		1.20	
H	0.006	0.012	0.15	0.30

SOT-563 (REV: R0)

R3 (9-May 2011)